

TLV1012

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SLCS154A -OCTOBER 2008-REVISED NOVEMBER 2008

# AMPLIFIER FOR HIGH-GAIN TWO-WIRE MICROPHONES

Check for Samples: TLV1012

## FEATURES

- Supply Voltage: 2 V to 5 V
- Supply Current: <180 μA
- Signal-to-Noise Ratio (A-Weighted): 60 dB
- Output Voltage Noise (A-Weighted): -89 dBV
- Total Harmonic Distortion: 0.013%
- Voltage Gain: 15.6 dB

## APPLICATIONS

- Cellular Phones
- Headsets
- Mobile Communications
- Automotive Accessories
- PDAs
- Accessory Microphone Products

YDC PACKAGE (TOP VIEW) OUTPUT 🖗 🖗 GND GND 🛞 🛞 INPUT

## **DESCRIPTION/ORDERING INFORMATION**

The TLV1012 is an audio amplifier series for small-form-factor electret microphones. This two-wire amplifier is designed to replace JFET amplifiers currently in use. The TLV1012 is ideally suited for applications that require high signal integrity in the presence of ambient or RF noise, such as in cellular communications. The TLV1012 audio amplifier is specified for operation over a 2.2-V to 5-V supply voltage range with a fixed gain of 15.6 dB. The device offers excellent THD, gain accuracy, and temperature stability compared to JFET microphones.

The TLV1012 enables a two-pin electret microphone solution, which provides direct pin-to-pin compatibility with the existing JFET market.

The TLV1012 is offered in a space-saving four-terminal ultra-thin lead-free package (YDC) and is ideally suited for the form factor of miniature electret microphone packages. The TLV1012 is characterized for operation over a free-air temperature range of –40°C to 85°C.

#### ORDERING INFORMATION<sup>(1)</sup>

	T <sub>A</sub>	A <sub>V</sub> <sup>(2)</sup>	(2) PACKAGE <sup>(3)</sup>		ORDERABLE PART NUMBER	TOP-SIDE MARKING	
-	–40°C to 85°C	15.6 dB	NanoStar™ WCSP (DSBGA) – YDC	Reel of 3000	TLV1012-15YDCR	Y38	

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

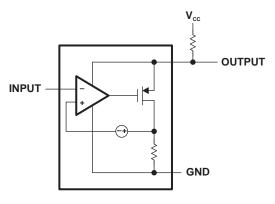
(2) Typical value measured at  $V_{DD}$  = 2.2 V,  $V_{IN}$  = 18 mV,  $R_L$  = 2.2 k $\Omega$ ,  $C_L$  = 2.2  $\mu$ F

(3) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.



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## ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup>

over operating free-air temperature range (unless otherwise noted)

$V_{CC}$	Supply voltage	–0.3 V to 5.5 V
V <sub>IN</sub>	Input voltage	–0.3 V to 0.3 V
$\theta_{JA}$	Thermal impedance, junction to free air <sup>(2)</sup>	230.47°C/W
T <sub>A</sub>	Operating free-air temperature range	–40°C to 85°C
T <sub>stg</sub>	Storage temperature range	–65°C to 150°C

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) Package thermal impedance is calculated according to JESD 51-5.

### **RECOMMENDED OPERATING CONDITIONS**

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage	2	5	V
T <sub>A</sub>	Operating free-air temperature	-40	85	°C

## 2.2-V ELECTRICAL CHARACTERISTICS

 $V_{CC}$  = 2.2 V,  $V_{IN}$  = 18 mV,  $R_L$  = 2.2 k $\Omega$  and  $C_L$  = 2.2  $\mu F$  (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	TJ	MIN	TYP	MAX	UNIT	
	Supply ourrent		25°C		150	240		
ICC	Supply current	V <sub>IN</sub> = GND	Full range			280	μA	
SNR	Signal-to-noise ratio	$f = 1 \text{ kHz}, V_{IN} = 18 \text{ mV}_{PP}, \text{ A-weighted}$	25°C		60		dB	
V <sub>IN</sub>	Maximum input signal	f = 1 kHz, THD+N < 1%	25°C		100		mV <sub>PP</sub>	
N/	Outeutualteas	V CND	25°C	1.70	1.87	1.94	V	
V <sub>OUT</sub>	Output voltage	V <sub>IN</sub> = GND	Full range	1.63		2.00		
f <sub>LOW</sub>	Lower –3-dB roll-off frequency	$R_{SOURCE} = 50 \ \Omega$	25°C		65		Hz	
f <sub>HIGH</sub>	Upper –3-dB roll-off frequency	$R_{SOURCE} = 50 \Omega$	25°C		95		kHz	
V <sub>N</sub>	Output noise	A-weighted	25°C		-89		dBV	
THD	Total harmonic distortion	$f = 1 \text{ kHz}, V_{IN} = 18 \text{ mV}_{PP}$	25°C		0.013		%	
C <sub>IN</sub>	Input capacitance		25°C		2		pF	
Z <sub>IN</sub>	Input impedance		25°C		>1000		GΩ	
٨	Coin		25°C	14.0	15.6	16.9	٩D	
A <sub>V</sub>	Gain	$f = 1 \text{ kHz}, \text{ R}_{\text{SOURCE}} = 50 \Omega$	Full range	13.1		17.5	dB	

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## **5-V ELECTRICAL CHARACTERISTICS**

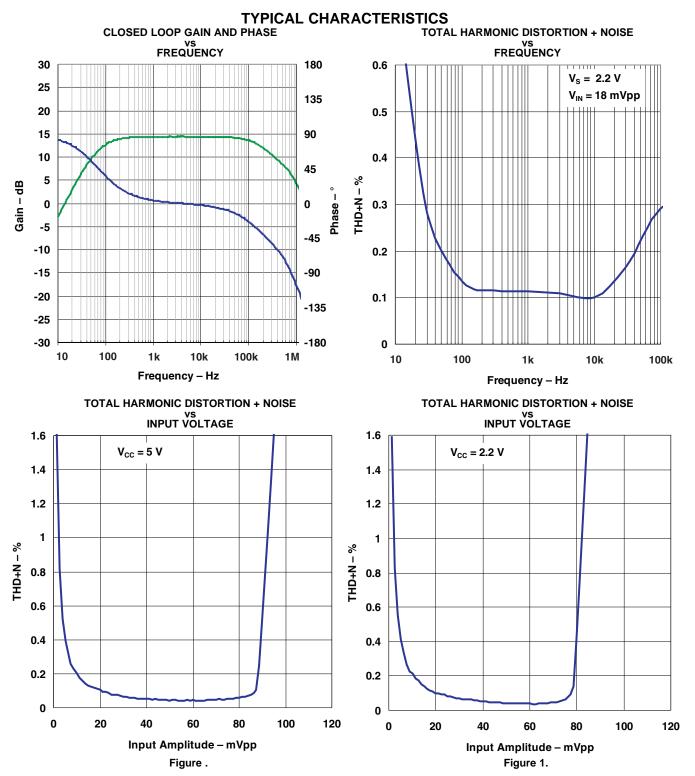
 $V_{CC}$  = 5 V,  $V_{IN}$  = 18 mV,  $R_L$  = 2.2  $k\Omega$  and  $C_L$  = 2.2  $\mu F$  (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	ТJ	MIN	TYP	MAX	UNIT
	Supply surrent	V CND	25°C		160	300	
I <sub>CC</sub>	Supply current	V <sub>IN</sub> = GND	Full range			325	μA
SNR	Signal-to-noise ratio	$f = 1 \text{ kHz}, V_{IN} = 18 \text{ mV}_{PP}, \text{ A-weighted}$	25°C		60		dB
V <sub>IN</sub>	Maximum input signal	f = 1 kHz, THD+N < 1%	25°C		100		mV <sub>PP</sub>
V	Output weltere	V CND	25°C	4.34	4.56	4.74	V
V <sub>OUT</sub>	Output voltage	V <sub>IN</sub> = GND	Full range	4.28		4.80	
f <sub>LOW</sub>	Lower –3-dB roll-off frequency	$R_{SOURCE} = 50 \Omega$	25°C		67		Hz
f <sub>HIGH</sub>	Upper –3-dB roll-off frequency	$R_{SOURCE} = 50 \Omega$	25°C		150		kHz
V <sub>N</sub>	Output noise	A-weighted	25°C		-89		dBV
THD	Total harmonic distortion	$f = 1 \text{ kHz}, V_{IN} = 18 \text{ mV}_{PP}$	25°C		0.013		%
CIN	Input capacitance		25°C		2		pF
Z <sub>IN</sub>	Input impedance		25°C		>1000		GΩ
•			25°C	14.0	15.6	16.9	
A <sub>V</sub>	Gain	$f = 1 \text{ kHz}, R_{\text{SOURCE}} = 50 \Omega$	Full range	13.1		17.5	dB



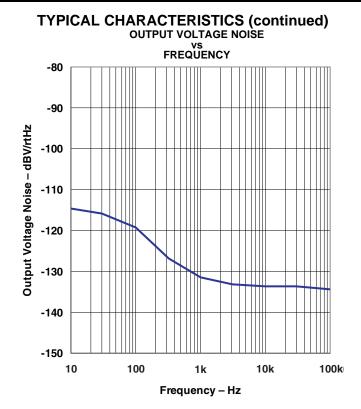
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### **APPLICATION INFORMATION**

### **High Gain**

The TLV1012 provides outstanding gain compared to JFET amplifiers and still maintains the same ease of implementation, with improved gain, linearity, and temperature stability. A high gain eliminates the need for extra external components.

#### Built-In Gain

The TLV1012 is offered in the space-saving YDC package, which fits perfectly into the metal can of a microphone. This allows the TLV1012 to be placed on the PCB inside the microphone.

The bottom side of the PCB usually shows a bull's-eye pattern, where the outer ring, which is shorted to the metal can, should be connected to the ground. The center dot on the PCB is connected to the  $V_{CC}$  through a resistor. This phantom biasing allows both supply voltage and output signal on one connection.

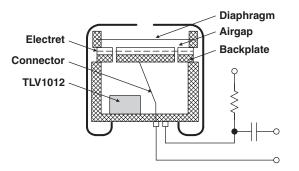


Figure 2. Built-In Gain

### A-Weighted Filter

The human ear has a frequency range from 20 Hz to about 20 kHz. Within this range the sensitivity of the human ear is not equal for each frequency. To approach the hearing response, weighting filters are introduced. One of those filters is the A-weighted filter.

The A-weighted filter is usually used in signal-to-noise ratio measurements, where sound is compared to device noise. It improves the correlation of the measured data to the signal-to-noise ratio perceived by the human ear.

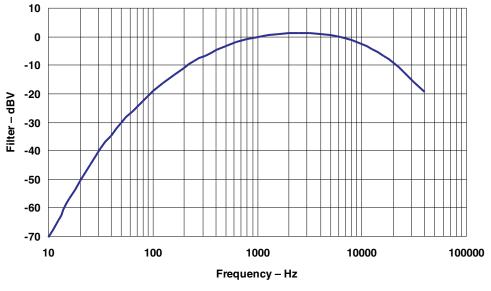


Figure 3. A-Weighted Filter



#### Measuring Noise and SNR

The overall noise of the TLV1012 is measured within the frequency band from 10 Hz to 22 kHz using an A-weighted filter. The input of the TLV1012 is connected to ground with a 5-pF capacitor.

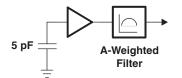


Figure 4. Noise Measurement

The signal-to-noise ratio (SNR) is measured with a 1 kHz input signal of 18 mV<sub>PP</sub> using an A-weighted filter. This represents a sound pressure level of 94 dBSPL. No input capacitor is connected.

#### Sound Pressure Level

The volume of sound applied to a microphone is usually stated as the pressure level with respect to the threshold of hearing of the human ear. The sound pressure level in decibels is defined by:

Sound pressure level (dB) =  $20 \log P_m/P_O$ 

Where  $P_m$  is the measured sound pressure, and  $P_O$  is the threshold of hearing (20  $\mu$ Pa).

To calculate the resulting output voltage of the microphone for a given sound pressure level, the sound pressure in dBSPL needs to be converted to the absolute sound pressure in dBPa. This is the sound pressure level in decibels, which is referred to as 1 Pascal (Pa).

The conversion is given by:

dBPa = dBSPL + 20 log 20 μPa dBPa = dBSPL – 94 dB

Translation from absolute sound pressure level to a voltage is specified by the sensitivity of the microphone. A conventional microphone has a sensitivity of –44 dBV/Pa.

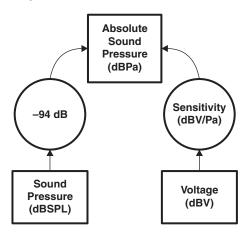


Figure 5. dB SPL to dBV Conversion

For example, busy traffic is 70 dBSPL:

 $V_{OUT} = 70 - 94 - 44 = -68 \text{ dBV}$ 

This is equivalent to 1.13 mV<sub>PP</sub>.

Because the TLV1012-15 has a gain of 6 (15.6 dB) over the JFET, the output voltage of the microphone is 6.78 mV<sub>PP</sub>. By replacing the JFET with the TLV1012-15, the sensitivity of the microphone is -28.4 dBV/Pa (-44 + 15.6).



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#### Low-Frequency Cut-Off Filter

To reduce noise on the output of the microphone, a low-cut filter is implemented in the TLV1012. This filter reduces the effect of wind and handling noise.

It is also helpful to reduce the proximity effect in directional microphones. This effect occurs when the sound source is very close to the microphone. The lower frequencies are amplified, which gives a bass sound. This amplification can cause an overload, which results in a distortion of the signal.

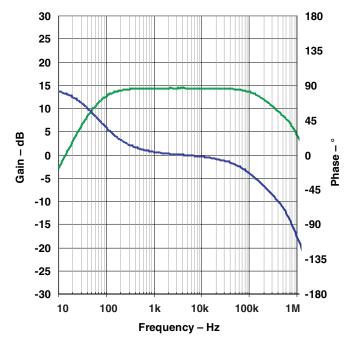


Figure 6. Gain and Phase vs Frequency

The TLV1012 is optimized to be used in audio-band applications. The TLV1012 provides a flat gain response within the audio band and offers linearity and excellent temperature stability.



#### Noise

Noise pick-up by a microphone in cell phones is a well known problem. A conventional JFET circuit is sensitive for noise pick-up because of its high output impedance, which is usually around 2.2 k $\Omega$ .

RF noise is among other noises caused by nonlinear behavior. The nonlinear behavior of the amplifier at high frequencies, well above the usable bandwidth of the device, causes AM demodulation of high-frequency signals. The AM modulation contained in such signals folds back into the audio band, thereby disturbing the intended microphone signal. The GSM signal of a cell phone is such an AM-modulated signal. The modulation frequency of 216 Hz and its harmonics can be observed in the audio band. This kind of noise is called bumblebee noise.

RF noise caused by a GSM signal can be reduced by connecting two external capacitors to ground (see Figure 7). One capacitor reduces the noise caused by the 900-MHz carrier, and the other reduces the noise caused by 1800/1900 MHz.

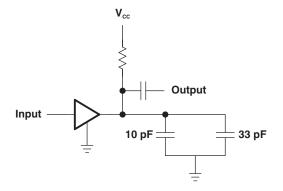


Figure 7. RF Noise Reduction



3-Nov-2013

## PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
TLV1012-15YDCR	OBSOLETE	DSBGA	YDC	4		TBD	Call TI	Call TI	-40 to 85	Y3 8	

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(<sup>6)</sup> Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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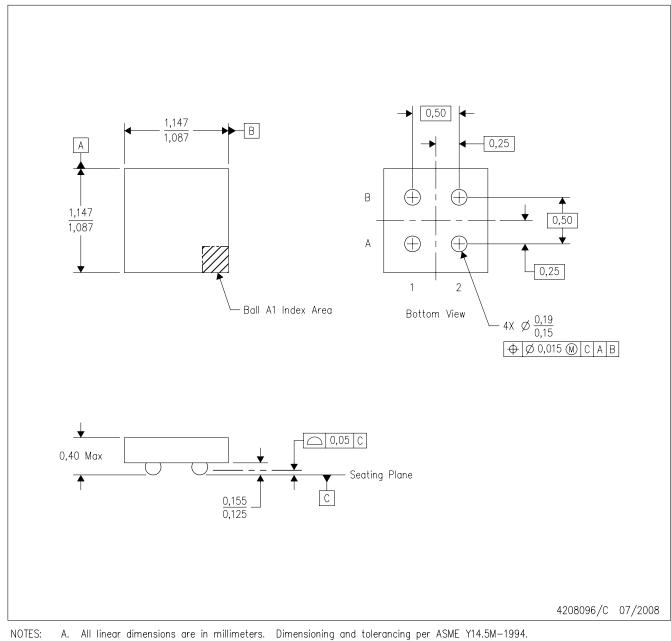
## PACKAGE OPTION ADDENDUM

3-Nov-2013

## **MECHANICAL DATA**

YDC (S-XBGA-N4)

DIE-SIZE BALL GRID ARRAY



- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.
- D. This package contains lead-free solder balls.

NanoFree is a trademark of Texas Instruments.



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